

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(substrate or semiconductor or wafer) and gas and "hexaethylamino-disilane" and ammonia and ("silicon nitride" or "SiN") and (438/778.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/19 14:30
L2	0	"hexaethylamino-disilane" and ammonia and ("silicon nitride" or "SiN") and (438/778.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/19 14:30
L3	0	"hexaethylamino-disilane" and ammonia and ("silicon nitride" or "SiN") and (438/778.ccls.)	US-PGPUB	OR	ON	2006/04/19 14:30
S1	137231	"CVD" and (heat\$4 or thermal\$4) and chamber and temperature and (supply or feed) and hexaethylaminodisilane and ammonia and gas "silicon nitride"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/18 10:07
S2	0	"CVD" and (heat\$4 or thermal\$4) and chamber and temperature and (supply or feed) and hexaethylaminodisilane and ammonia and gas and "silicon nitride"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 12:47
S3	0	(heat\$4 or thermal\$4) and chamber and temperature and (supply or feed) and hexaethylaminodisilane and ammonia and gas and "silicon nitride"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 12:47
S4	3	"hexaethylaminodisilane"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 12:47
S5	1	"hexaethylaminodisilane" and heat and substrate and chamber	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 09:22

EAST Search History

S6	6	"6475902"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 09:23
S7	427311	"CVD" and (heat\$4 near4 (substrate or semiconductor or wafer)) and temperature and (gas near4 hexaethylaminodisilane) and ammonia ("silicon nitride" or "SiN")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/18 10:09
S8	2	"CVD" and (heat\$4 near4 (substrate or semiconductor or wafer)) and temperature and (gas near4 hexaethylaminodisilane) and ammonia and ("silicon nitride" or "SiN")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/18 10:10
S9	3	(heat\$4 near4 (substrate or semiconductor or wafer)) and temperature and (gas near4 hexaethylaminodisilane) and ammonia and ("silicon nitride" or "SiN")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/18 10:13
S10	3	(substrate or semiconductor or wafer) and temperature and (gas near4 hexaethylaminodisilane) and ammonia and ("silicon nitride" or "SiN")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/18 10:14
S11	2	((heat or thermal) near4 (substrate or semiconductor or wafer)) and gas and hexaethylaminodisilane and ammonia and ("silicon nitride" or "SiN")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/18 10:22
S12	3	(substrate or semiconductor or wafer) and gas and hexaethylaminodisilane and ammonia and ("silicon nitride" or "SiN")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/18 10:22
S13	1	(substrate or semiconductor or wafer) and gas and "hexaethylamino-disilane" and ammonia and ("silicon nitride" or "SiN")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/19 14:29